

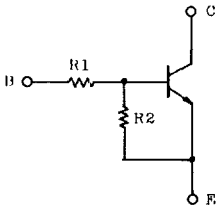
RN1007, 1008, 1009

SWITCHING, INVERTER CIRCUIT, INTERFACE CIRCUIT
AND DRIVER CIRCUIT APPLICATIONS.

FEATURES:

- . With Built-in Bias Resistors
- . Simplify Circuit Design
- . Reduce a Quantity of Parts and Manufacturing Process
- . Complementary to RN2007~2009

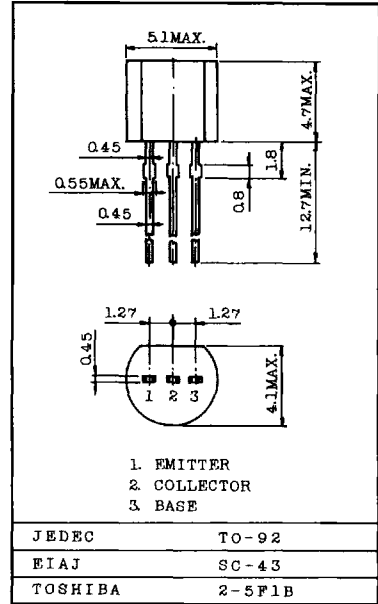
EQUIVALENT CIRCUIT



BIAS RESISTOR VALUES

TYPE No.	R1 (kΩ)	R2 (kΩ)
RN1007	10	47
RN1008	22	47
RN1009	47	22

Unit in mm



Weight : 0.21g

MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V _{CB0}	50	V
Collector-Emitter Voltage	V _{CE0}	50	V
Emitter-Base Voltage	RN1007	6	V
	RN1008	7	
	RN1009	15	
Collector Current	I _C	100	mA
Collector Power Dissipation	P _C	400	mW
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _{stg}	-55~150	°C

ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		ICBO	V _{CB} =50V, I _E =0	-	-	100	nA
		ICEO	V _{CE} =50V, I _B =0	-	-	500	nA
Emitter Cut-off Current	RN1007	IEBO	V _{EB} =6V, I _C =0	0.081	-	0.15	mA
	RN1008			0.078	-	0.145	
	RN1009			0.167	-	0.311	
DC Current Gain	RN1007	hFE	V _{CE} =5V, I _C =10mA	80	-	-	-
	RN1008			80	-	-	
	RN1009			70	-	-	
Collector-Emitter Saturation Voltage		V _{CE(sat)}	I _C =5mA, I _B =0.25mA	-	0.1	0.3	V
Input Voltage (ON)	RN1007	V _{I(ON)}	V _{CE} =0.2V, I _C =5mA	0.7	-	1.8	V
	RN1008			1.0	-	2.6	
	RN1009			2.2	-	5.8	
Input Voltage (OFF)	RN1007	V _{I(OFF)}	V _{CE} =5V, I _C =0.1mA	0.5	-	1.0	V
	RN1008			0.6	-	1.16	
	RN1009			1.5	-	2.6	
Transition Frequency		f _T	V _{CE} =10V, I _C =5mA	-	250	-	MHz
Collector Output Capacitance		C _{ob}	V _{CB} =10V, I _E =0 f=1MHz	-	3	6	pF
Input Resistor	RN1007	R ₁		7	10	13	kΩ
	RN1008			15.4	22	28.6	
	RN1009			32.9	47	61.1	
Resistor Ratio	RN1007	R ₁ /R ₂		0.191	0.213	0.232	-
	RN1008			0.421	0.468	0.515	
	RN1009			1.92	2.14	2.35	

